

IRFB4110PBF(ES)

Rev-1.4

SuperMOS –TO-220 100V BV_{DSS} , $4.2m\Omega$ $R_{DS(on)}$, N-channel MOSFET

1. Description

The IRFB4110PBF(ES) is N-Channel enhancement MOS Field Effect Transistor. Using advanced shielded gate trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product IRFB4110PBF(ES) is Pb-free.

2. Features

- 100V, $R_{DS(on)}=4.2m\Omega$ (TYP.) @ $V_{GS}=10V$
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per Tube	Flammability Rating
IRFB4110PBF(ES)	TO-220	GNU10R042/lot	Halogen free	Tube	50 PCS	UL 94V-0

Table-1 Ordering information

5. Pin Configuration and Functions

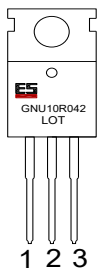
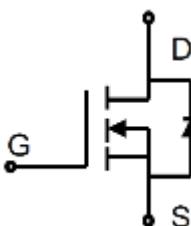
Pin	Function	Outline	Circuit Diagram
1	Gate	Note 1 	
3	Source		
2	Drain		

Table-2 Pin configuration

IRFB4110PBF(ES)

Rev-1.4

Note1:

This diagram is only an electrical schematic, and the actual pin size is based on POD.

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^{\circ}\text{C}$, Silicon limit	I_D	182	A
	$T_C=25^{\circ}\text{C}$, Package limit		180	
	$T_C=100^{\circ}\text{C}$, Silicon limit		115	
Maximum Power Dissipation		P_D	278	W
Pulsed Drain Current		I_{DM}	720	A
Avalanche energy		E_{AS}	702	mJ
Operating Junction Temperature		T_J	-55 to 150	$^{\circ}\text{C}$
Lead Temperature		T_L	260	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance ratings

Single Operation			
Parameter	Symbol	Typical	Unit
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	0.45	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^{\circ}\text{C}/\text{W}$

IRFB4110PBF(ES)

Rev-1.4

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1.0	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	2.5		4.5	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =10V, I _D =50A		3.45	4.2	mΩ
Forward transconductance	g _{fs}	V _{DS} =5V, I _D =50A		94		
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, f=250KHz, V _{DS} =50V		7116		pF
Output Capacitance	C _{OSS}			1067		
Reverse Transfer Capacitance	C _{RSS}			24		
Total Gate Charge	Q _{G(TOT)}	V _{GS} =10V, V _{DS} =80V, I _D =50A		115		nC
Gate-to-Source Charge	Q _{GS}			28		
Gate-to-Drain Charge	Q _{GD}			33		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DD} =50V, I _D =50A, R _g =10Ω		75		ns
Rise Time	t _r			176		
Turn-Off Delay Time	t _{d(OFF)}			110		
Fall Time	t _f			66.7		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =50A			1.1	V

7. Typical Characteristic

Figure 1. Typ. Output Characteristics

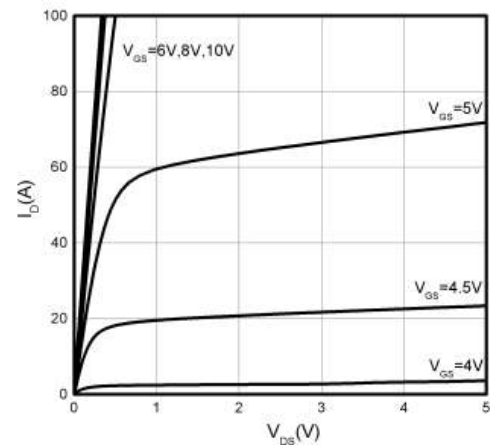


Figure 2. Transfer Characteristics

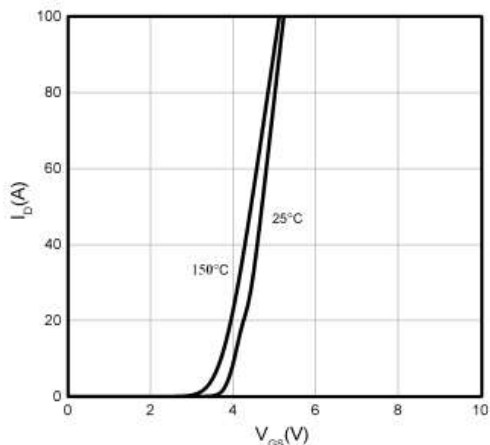


Figure 3. On-Resistance vs. Drain Current

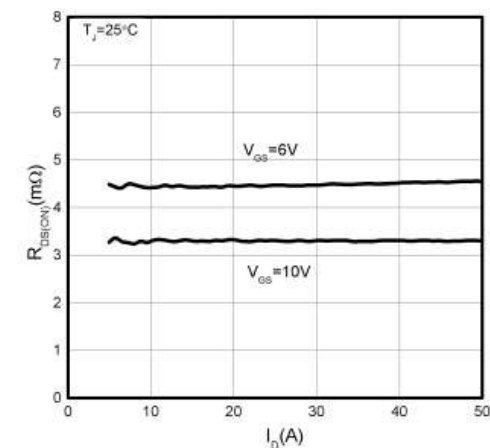


Figure 4. On-Resistance vs. Temperature

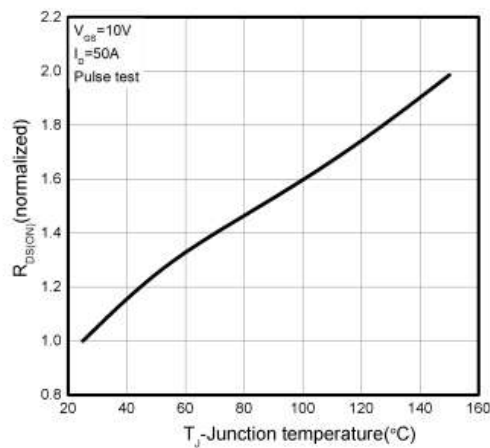


Figure 5. Rds(on) vs. Gate Voltage

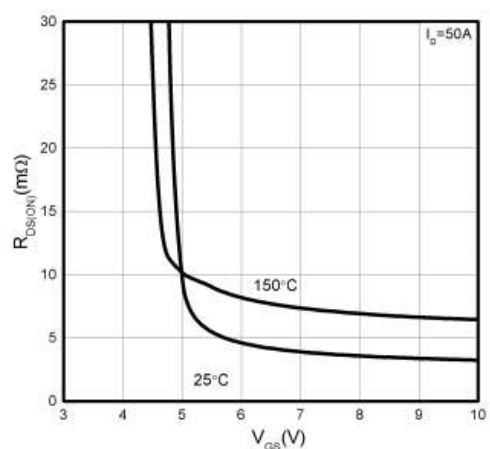


Figure 6. Body-Diode Characteristics

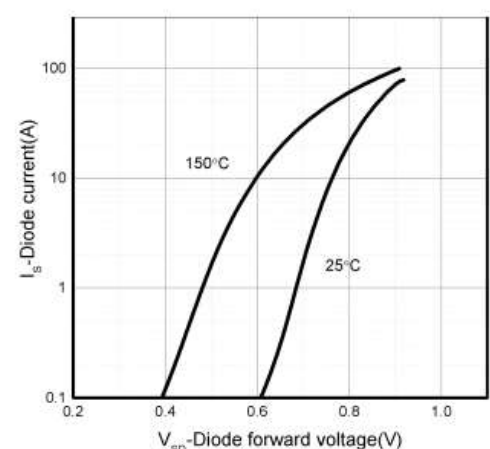
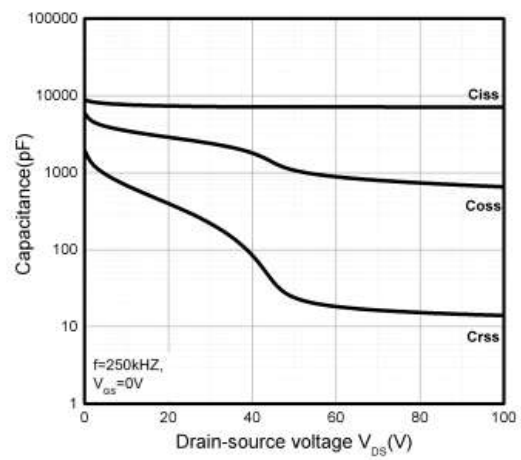


Figure 7. Capacitance Characteristics

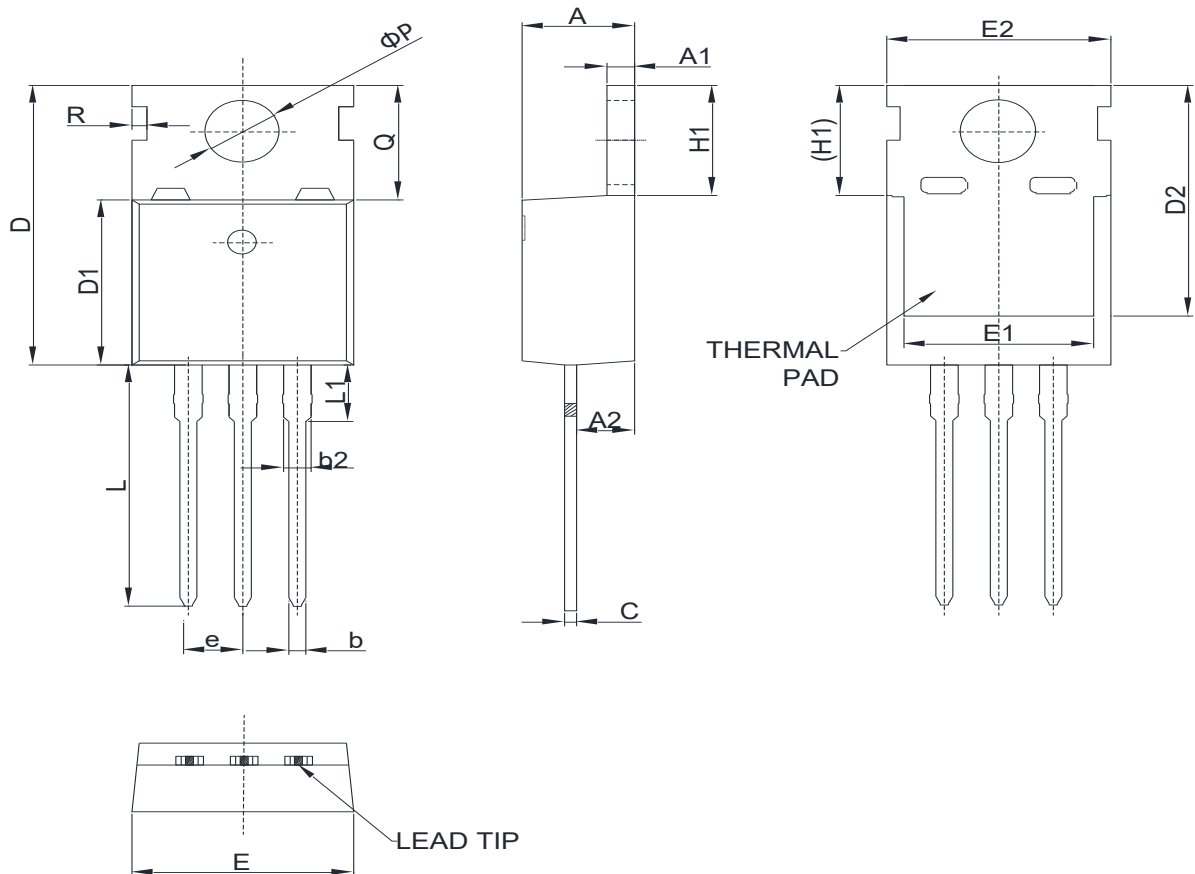


IRFB4110PBF(ES)

Rev-1.4

8. Dimension (TO-220)

POD A(Q)

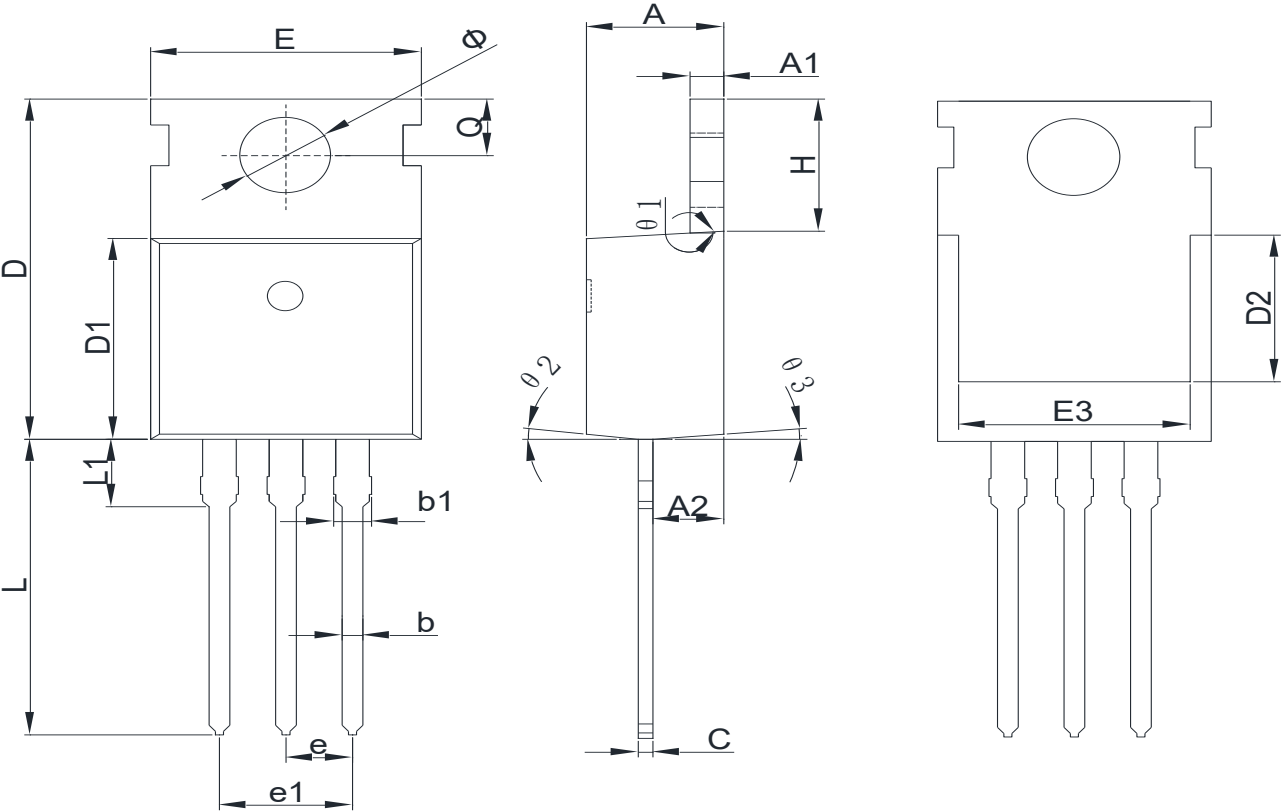


COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER							
SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.47	4.57	4.67	L1	3.56	3.76	3.96
A1	1.17	1.27	1.37	L	13.15	13.45	13.75
A2	2.52	2.67	2.82	H1	6.00	6.30	6.60
c	0.360	0.381	0.500	P	3.70	3.84	3.95
D	15.00	15.30	15.60	Q	2.60	2.74	2.90
D1	8.70	9.00	9.30	R	0.00	0.20	0.35
D2	12.19	12.39	12.60	E1	7.98	8.18	8.48
E	9.70	9.92	10.30	b	0.71	0.81	0.91
E2	9.85	10.00	10.15	b2	1.17	1.27	1.37
e	2.44	2.54	2.64				

IRFB4110PBF(ES)

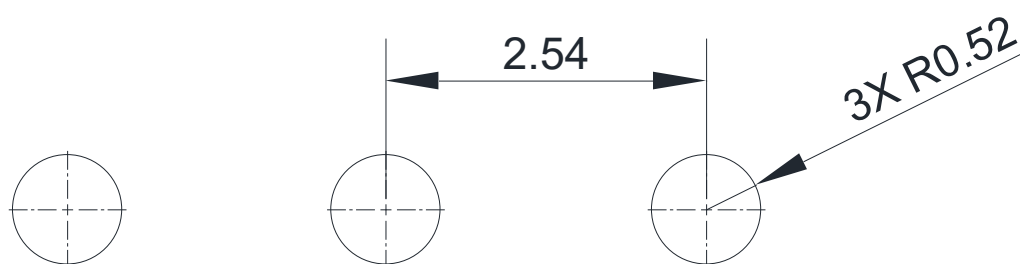
Rev-1.4

POD B(X)



MILLIMETERS							
SYMBOLS	MIN	TYP	MAX	SYMBOLS	MIN	TYP	MAX
A	4.37	4.57	4.70	E	9.70	10.00	10.30
A1	1.25	1.30	1.40	E3	7.00	7.60REF	
A2	2.15	2.35	2.55	e	2.54BSC		
b	0.70	0.80	0.95	e1	5.08BSC		
b1	1.17	1.27	1.47	H	6.25	6.50	6.75
c	0.45	0.50	0.60	L	13.20	13.50	13.80
D	15.10	15.60	16.10	L1		3.10	3.40
D1	8.80	9.10	9.40	θ 1	7° TYP		
D2	5.50	6.30REF		θ 2	7° TYP		
Φ	3.40	3.60	3.80	θ 3	3° TYP		
Q	2.60	2.80	3.00				

9. Recommendation of Hole Pattern



DIMENSIONS: MILLIMETERS

DISCLAIMER

ELECSUPER PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with ElecSuper products. You are solely responsible for

(1) selecting the appropriate ElecSuper products for your application;

(2) designing, validating and testing your application;

(3) ensuring your application meets applicable standards, and any other safety, security, or other requirements.

These resources are subject to change without notice. ElecSuper grants you permission to use these resources only for development of an application that uses the ElecSuper products described in the resource. Other reproduction and display of these resources are prohibited. No license is granted to any other ElecSuper intellectual property right or to any third party intellectual property right. ElecSuper disclaims responsibility for, and you will fully indemnify ElecSuper and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources. ElecSuper's products are provided subject to ElecSuper's Terms of Sale or other applicable terms available either on www.elecsuper.com or provided in conjunction with such ElecSuper products. ElecSuper's provision of these resources does not expand or otherwise alter ElecSuper's applicable warranties or warranty disclaimers for ElecSuper products.